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-		or US-6611405-\$ or US-6636399-\$ or US-6710984-\$ or US-6707711-\$ or US-6555889-\$ or US-5650958-\$).did. or (US-20040095690-\$ or US-20010040778-\$).did. (mram or memory) and (lower or bottom) near3 (electrode or conductor) near4 (trench or groove) (mram or magnetic near memory) and (lower or bottom) near2 (electrode or conductor) near2	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	
		or US-6611405-\$ or US-6636399-\$ or US-6710984-\$ or US-6707711-\$ or US-6555889-\$ or US-5650958-\$).did. or (US-20040095690-\$ or US-20010040778-\$).did. (mram or memory) and (lower or bottom) near3 (electrode or conductor) near4 (trench or groove) (mram or magnetic near memory) and (lower or bottom) near2 (electrode or conductor) near2 (trench or groove)	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/21 08:45
		or US-6611405-\$ or US-6636399-\$ or US-6710984-\$ or US-6707711-\$ or US-6555889-\$ or US-5650958-\$).did. or (US-20040095690-\$ or US-20010040778-\$).did. (mram or memory) and (lower or bottom) near3 (electrode or conductor) near4 (trench or groove) (mram or magnetic near memory) and (lower or bottom) near2 (electrode or conductor) near2 (trench or groove) (mram or magnetic near memory) and (lower or bottom) near2 (electrode or conductor) near2 (trench or groove)	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2004/06/21 08:45
		or US-6611405-\$ or US-6636399-\$ or US-6710984-\$ or US-6707711-\$ or US-6555889-\$ or US-5650958-\$).did. or (US-20040095690-\$ or US-20010040778-\$).did. (mram or memory) and (lower or bottom) near3 (electrode or conductor) near4 (trench or groove) (mram or magnetic near memory) and (lower or bottom) near2 (electrode or conductor) near2 (trench or groove) (mram or magnetic near memory) and (lower or bottom) near2 (electrode or conductor) near2	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB;	2004/06/21 08:45
		or US-6611405-\$ or US-6636399-\$ or US-6710984-\$ or US-6707711-\$ or US-6555889-\$ or US-5650958-\$).did. or (US-20040095690-\$ or US-20010040778-\$).did. (mram or memory) and (lower or bottom) near3 (electrode or conductor) near4 (trench or groove) (mram or magnetic near memory) and (lower or bottom) near2 (electrode or conductor) near2 (trench or groove) (mram or magnetic near memory) and (lower or bottom) near2 (electrode or conductor) near2 (within or recessed or recess or grooved or	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/06/21 08:45
		or US-6611405-\$ or US-6636399-\$ or US-6710984-\$ or US-6707711-\$ or US-6555889-\$ or US-5650958-\$).did. or (US-20040095690-\$ or US-20010040778-\$).did. (mram or memory) and (lower or bottom) near3 (electrode or conductor) near4 (trench or groove) (mram or magnetic near memory) and (lower or bottom) near2 (electrode or conductor) near2 (trench or groove) (mram or magnetic near memory) and (lower or bottom) near2 (electrode or conductor) near2	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB;	2004/06/21 08:41 2004/06/21 08:45 2004/06/21 08:46